ON Semiconductor®

J111 / J112 / J113 / MMBFJ111 / MMBFJ112 / MMBFJ113
N-Channel Switch

Features

- This device is designed for low level analog switching, sample and hold circuits and chopper stabilized amplifiers.
- Sourced from process 51
- Source & Drain are interchangeable.

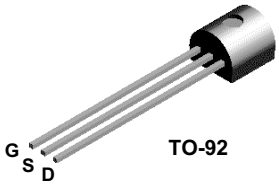


Figure 1. J111 / J112 / J113 Device Package

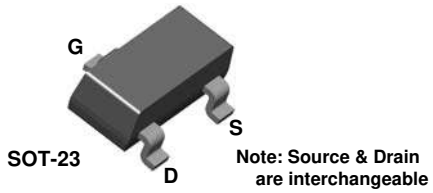


Figure 2. MMBFJ111 / MMBFJ112 / MMBFJ113 Device Package

Ordering Information

Part Number	Top Mark	Package	Packing Method
J111	J111	TO-92 3L	Bulk
J111-D26Z	J111	TO-92 3L	Tape and Reel
J111-D74Z	J111	TO-92 3L	Ammo
J112	J112	TO-92 3L	Bulk
J112-D26Z	J112	TO-92 3L	Tape and Reel
J112-D27Z	J112	TO-92 3L	Tape and Reel
J112-D74Z	J112	TO-92 3L	Ammo
J113	J113	TO-92 3L	Bulk
J113-D74Z	J113	TO-92 3L	Ammo
J113-D75Z	J113	TO-92 3L	Ammo
MMBFJ111	6P	SOT-23 3L	Tape and Reel
MMBFJ112	6R	SOT-23 3L	Tape and Reel
MMBFJ113	6S	SOT-23 3L	Tape and Reel

October-2017, Rev. 2

Publication Order Number:
MMBFJ113/D

Absolute Maximum Ratings[1], [2]

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	35	V
V_{GS}	Gate-Source Voltage	-35	V
I_{GF}	Forward Gate Current	50	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C

Notes:

1. These ratings are based on a maximum junction temperature of 150°C.
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.		Unit
		J111 / **J112** / **J113**[3]	**MMBFJ111** / **MMBFJ112** / **MMBFJ113**[4]	
P_D	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	357	°C/W

Notes:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
4. Device mounted on FR-4 PCB 36mm × 18mm × 1.5mm; mounting pad for the collector lead minimum 6cm^2.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Max.	Unit
Off Characteristics						
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = -1.0 μA, V_{DS} = 0		-35		V
I_{GSS}	Gate Reverse Current	V_{GS} = -15 V, V_{DS} = 0			-1.0	nA
V_{GS}(off)	Gate-Source Cut-Off Voltage	V_{DS} = 15 V, I_D = 1.0 μA	**111**	-3.0	-10.0	V
			112	-1.0	-5.0	
			113	-0.5	-3.0	
I_D(off)	Drain Cutoff Leakage Current	V_{DS} = 5.0 V, V_{GS} = -10 V			1.0	nA
On Characteristics						
I_{DSS}	Zero-Gate Voltage Drain Current[5]	V_{DS} = 15 V, V_{GS} = 0	**111**	20		mA
			112	5.0		
			113	2.0		
r_{DS}(on)	Drain-Source On Resistance	V_{DS} ≤ 0.1 V, V_{GS} = 0	**111**		30	Ω
			112		50	
			113		100	
Small Signal Characteristics						
C_{dg}(on) C_{sg}(on)	Drain-Gate &Source-Gate On Capacitance	V_{DS} = 0, V_{GS} = 0, f = 1.0 MHz			28	pF
C_{dg}(off)	Drain-Gate Off Capacitance	V_{DS} = 0, V_{GS} = -10 V, f = 1.0 MHz			5.0	pF
C_{sg}(off)	Source-Gate Off Capacitance	V_{DS} = 0, V_{GS} = -10 V, f = 1.0 MHz			5.0	pF

Note:

5. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

Typical Performance Characteristics

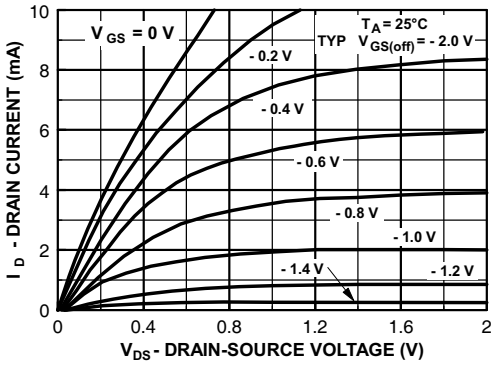


Figure 3. Common Drain-Source

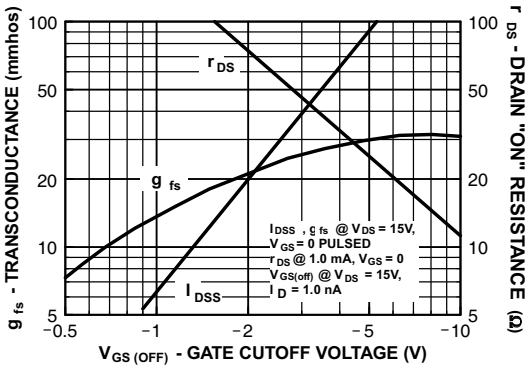


Figure 4. Parameter Interactions

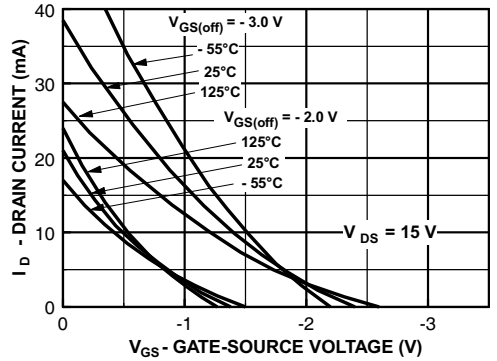


Figure 5. Transfer Characteristics

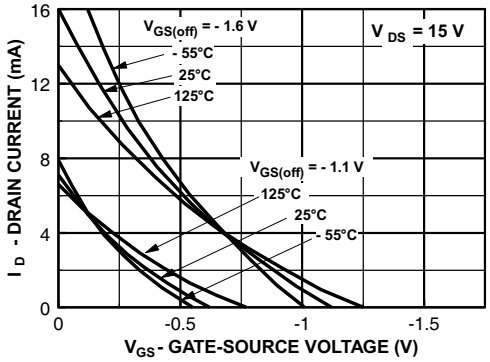


Figure 6. Transfer Characteristics

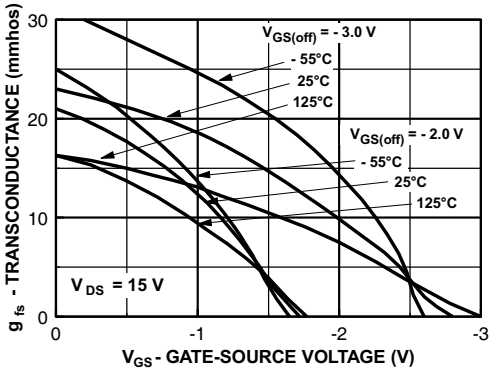


Figure 7. Transfer Characteristics

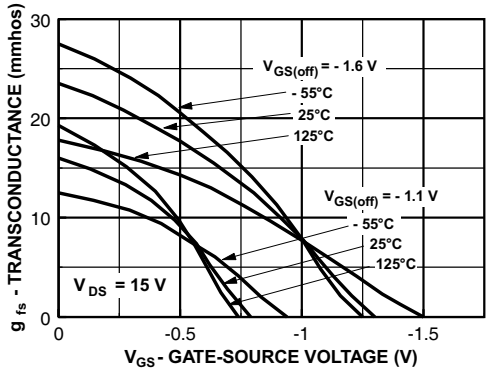


Figure 8. Transfer Characteristics

Typical Performance Characteristics (Continued)

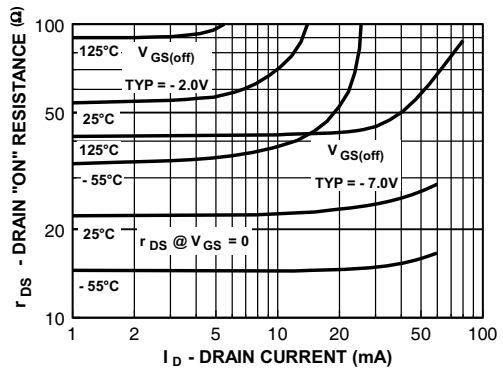


Figure 9. On Resistance vs. Drain Current

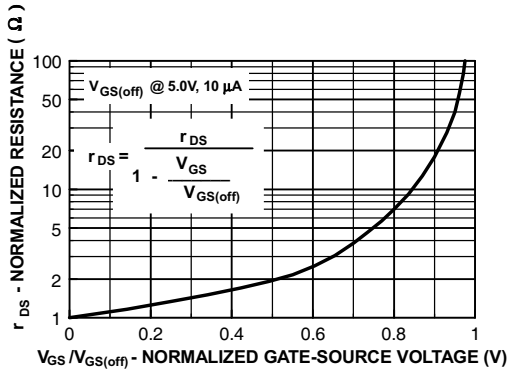


Figure 10. Normalized Drain Resistance vs. Bias Voltage

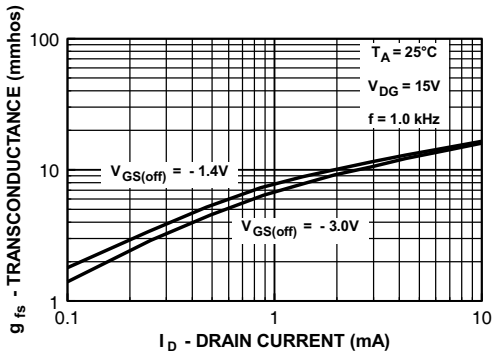


Figure 11. Transconductance vs. Drain Current

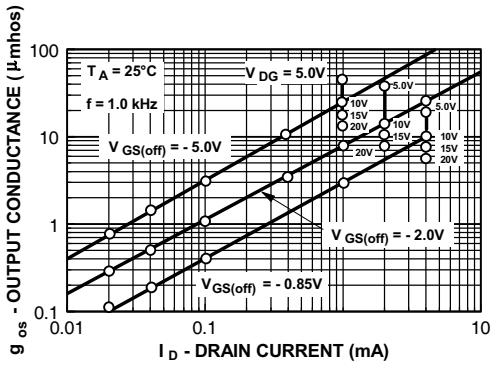


Figure 12. Output Conductance vs. Drain Current

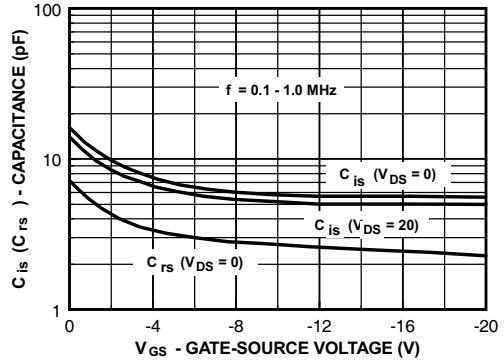


Figure 13. Capacitance vs. Voltage

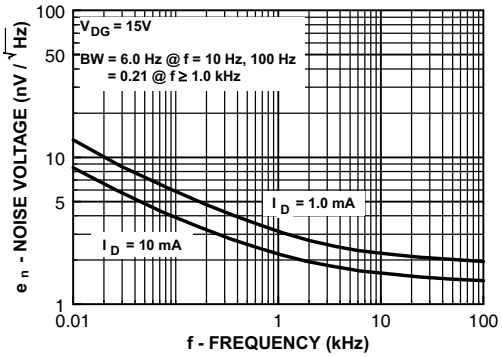


Figure 14. Noise Voltage vs. Frequency

Typical Performance Characteristics (Continued)

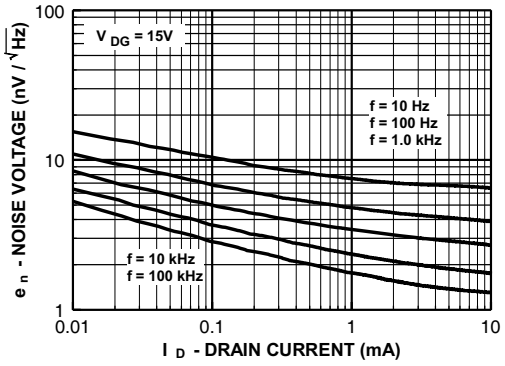


Figure 15. Noise Voltage vs. Current

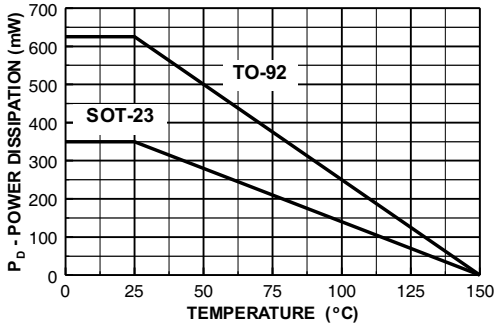


Figure 16. Power Dissipation vs. Ambient Temperature

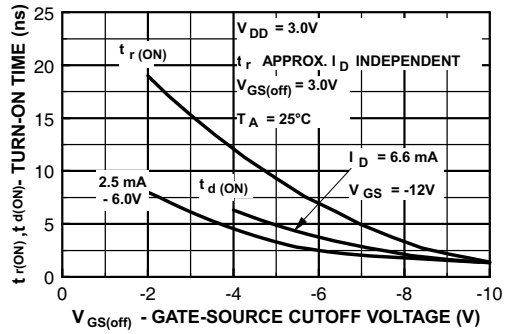


Figure 17. Switching Turn-On Time vs. Gate-Source Voltage

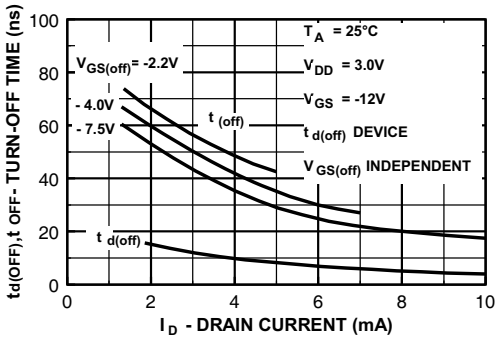
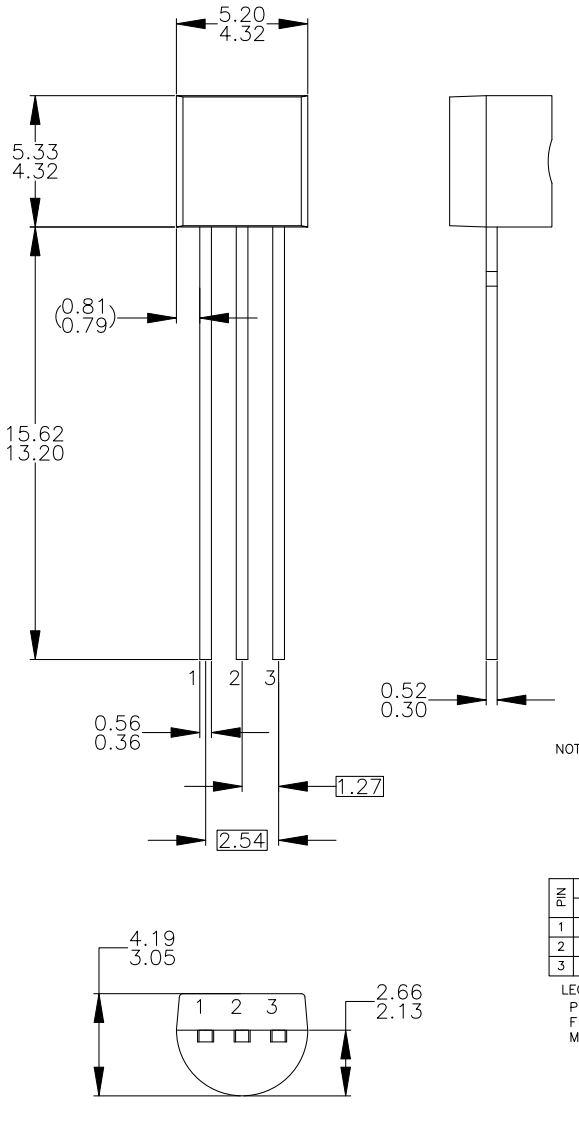


Figure 18. Switching Turn-Off Time vs. Drain Current

Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

A) DRAWING WITH REFERENCE TO JEDEC TO−92 RECOMMENDATIONS.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M−1994.
D) TO−92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	B	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

LEGEND:
P − BIPOLAR
F − JFET
M − DMOS
E − EMITTER
B − BASE
C − COLLECTOR
D − DRAIN
S − SOURCE
G − GATE

E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEAGLE AT JFET "F" OPTION.
F) DRAWING FILENAME: MKT−ZA03DREV3.

Figure 19. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)

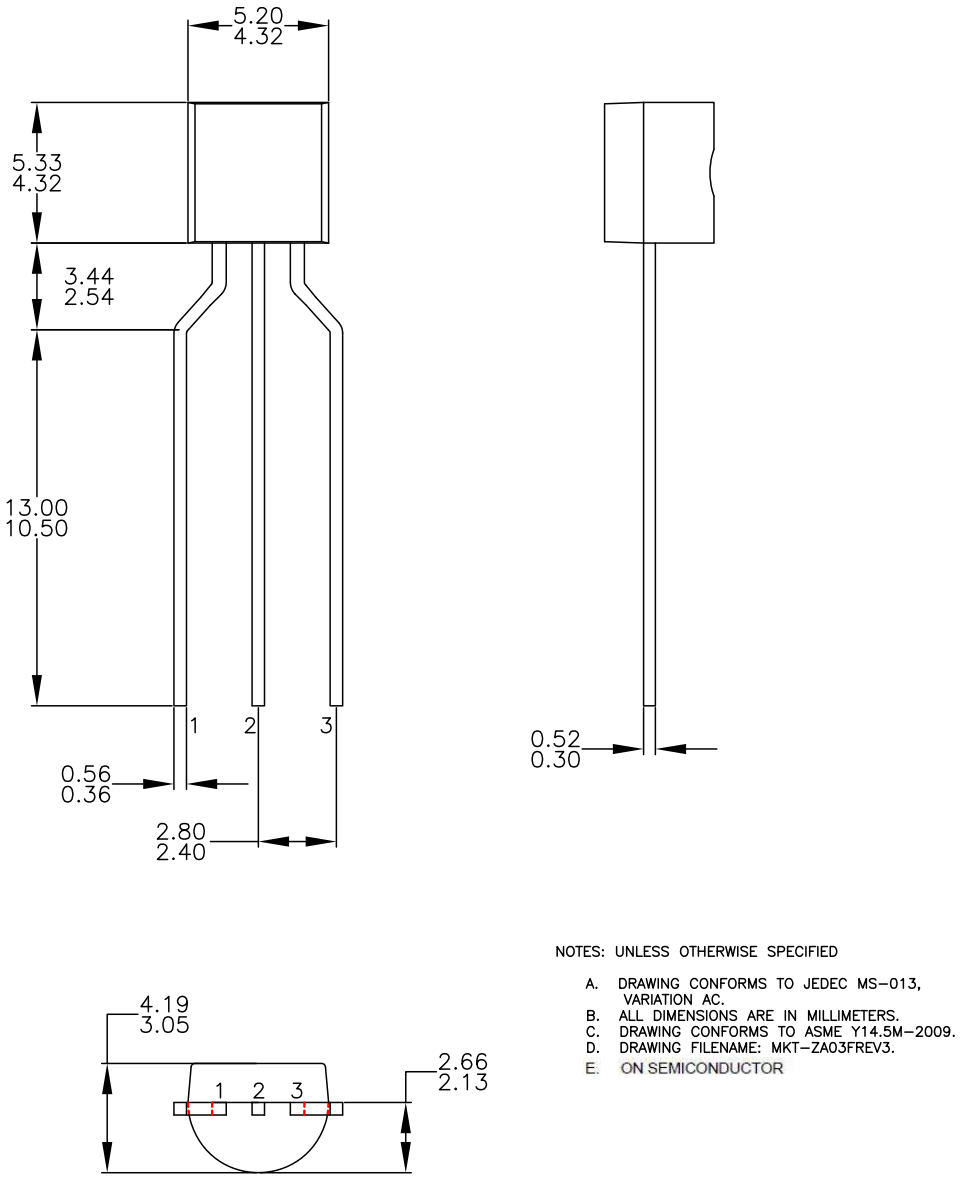


Figure 20. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type

Physical Dimensions (Continued)

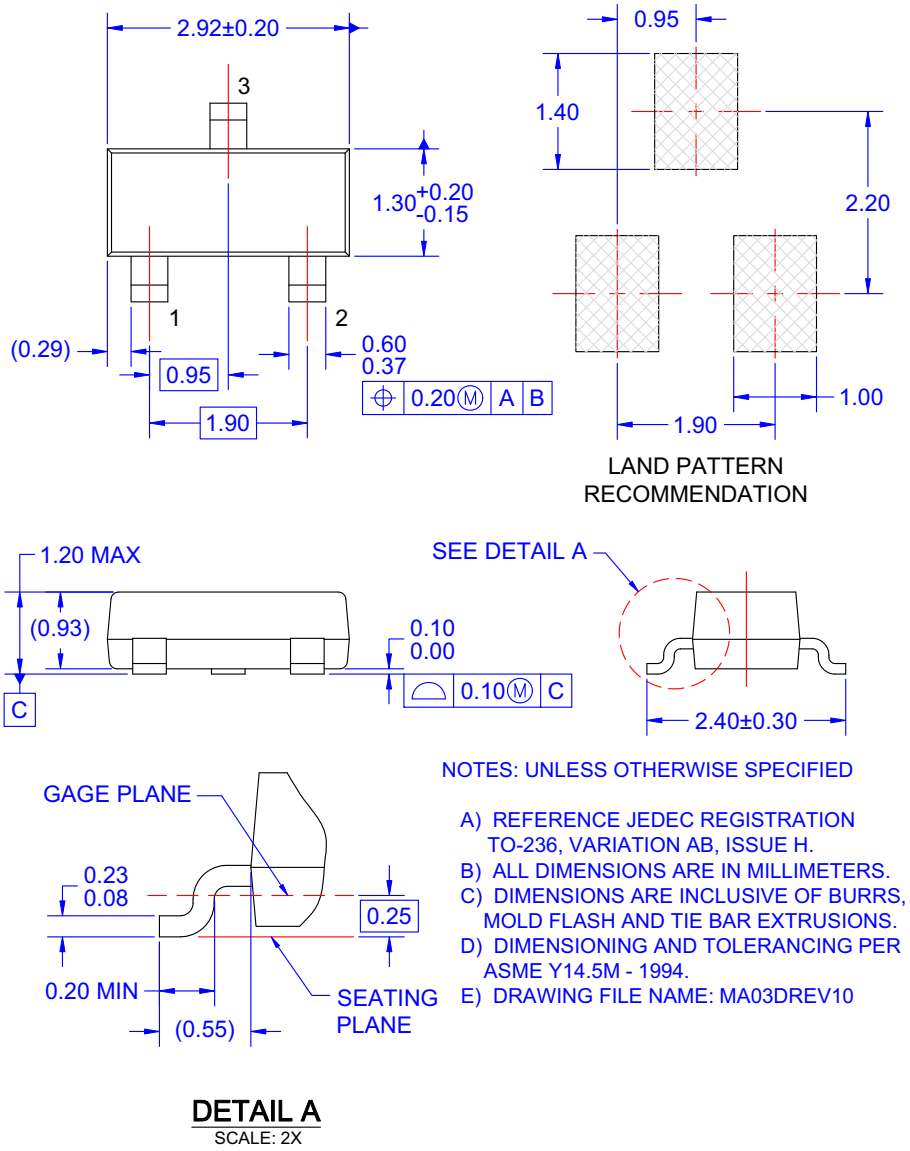


Figure 21. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

PUBLICATION ORDERING INFORMATION

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